

ABSTRACT OF THE DISCLOSURE

The present invention is directed to a method of fabricating a capacitor having a metal/insulator/metal (MIM) structure, which is capable of providing a minimized semiconductor device with no capacitance variation of a capacitor. According to an aspect of the present invention, a method of fabricating a thin film capacitor comprises the steps of forming a first via and a second via which are isolated with a predetermined distance by selectively etching an interlayer insulating film formed over the entire structure of a semiconductor substrate, filling in the first via and the second via with a first metal material, forming a capacitor window by etching the interlayer insulating film between the first via and the second via to have a predetermined depth, forming a dielectric layer on an inner wall, and forming a second metal material to fill in the capacitor window.